

Notice of References Cited		Application/Control No:	Applicant(s)/Patent Under Reexamination ITANO ET AL.	
		Examiner TabassomT Tadayyon-Eslami	Art Unit 1709	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	B	US-5,120,605	06-1992	Zuel et al.	428/410
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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.